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Resistive Switching: From Fundamentals of Nanoionic Redox Processes to Memristive Device Applications, First Edition. Edited by Daniele Ielmini and Rainer Waser. © 2016 Wiley-VCH Verlag GmbH & Co. KGaA. Published 2016 by Wiley-VCH Verlag GmbH & Co. KGaA.

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